



IRFI634GPBF Information



For Reference Only

Part Number IRFI634GPBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 250V 5.6A TO220FPPackageTO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRFI634GPBF Specifications

Manufacturer Part Number IRF1634GPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 5.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 41nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 770pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 770pF @ 25V Vgs (Max) #20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature MosfET (Semiconductor Products To-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	IRFI634GPBF
Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 5.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 41nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 770pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer	Vishay Siliconix
PackageTO-220-3 Full Pack, Isolated TabSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs4lnC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs4lnC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs As On (Max) @ Id, Vgs As On (Max) @ Id, Vgs Through Hole Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) ANOSFET (Metal Oxide) ANOSFET (Metal Oxide) ANOSFET (Metal Oxide) 5.6A (Tc) 6.A (Tc) 6.	Package	TO-220-3 Full Pack, Isolated Tab
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs41nC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Series	-
Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs41nC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs41nC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs41nC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 770pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	5.6A (Tc)
Gate Charge (Qg) (Max) @ Vgs 41nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 770pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 770pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	41nC @ 10V
FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	770pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 450 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs450 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	35W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	450 mOhm @ 3.4A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

IRFI634GPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFI634GPBF Payment Methods



















IRFI634GPBF Shipping Methods













If you have any question about IRFI634GPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com